

D³

9. (Amended) A semiconductor device according to claim 7 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

D⁴

13. (Amended) A semiconductor device according to claim 12 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

D⁵

16. (Amended) A semiconductor device according to claim 15 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

D⁶

19. (Amended) A semiconductor device according to claim 18 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.